AMENDMENTS TO THE CLAIMS

Claims 1-9 canceled.

10. (New) An epitaxial growth method comprising: supporting a substrate for growth with a substrate supporter, forming a compound semiconductor layer comprising 3 or 4 elements on the substrate for growth by metal organic chemical vapor deposition, polishing the substrate so that an angle of gradient is 0.00° to 0.03° or 0.04° to 0.10° with respect to (100) direction in an entire effective area of the substrate, and forming the compound semiconductor layer to be 0.5μm thick or more on the substrate by using the substrate for growth.

11. (New) The epitaxial growth method as claimed in claim 10, further comprising: forming a buffer layer on the substrate for growth, and forming the compound semiconductor layer on the buffer layer.

12. (New) The epitaxial growth method as claimed in claim 10, wherein the compound semiconductor layer is a III-V group compound semiconductor layer containing at least As.

13. (New) The epitaxial growth method as claimed in claim 11, wherein the compound semiconductor layer is a III-V group compound semiconductor layer containing at least As.

14. (New) The epitaxial growth method as claimed in claim 12, wherein the compound semiconductor layer is an InGaAs layer or an InAlAs layer.

15. (New) The epitaxial growth method as claimed in claim 13, wherein the compound semiconductor layer is an InGaAs layer or an InAlAs layer.

16. (New) The epitaxial growth method as claimed in claim 12, wherein the substrate for growth is a semiconductor crystal substrate having dislocation density of $5000cm^{-2}$ or less.

17. (New) The epitaxial growth method as claimed in claim 13, wherein the substrate for growth is a semiconductor crystal substrate having dislocation density of $5000cm^{-2}$ or less.

18. (New) The epitaxial growth method as claimed in claim 14, wherein the substrate for growth is a semiconductor crystal substrate having dislocation density of $5000cm^{-2}$ or less.

19. (New) The epitaxial growth method as claimed in claim 15, wherein the substrate for growth is a semiconductor crystal substrate having dislocation density of $5000cm^{-2}$ or less.

20. (New) The epitaxial growth method as claimed in claim 16, wherein the substrate for growth is an InP substrate.

21. (New) The epitaxial growth method as claimed in claim 17, wherein the substrate for growth is an InP substrate.

22. (New) The epitaxial growth method as claimed in claim 18, wherein the substrate for

growth is an InP substrate.

23. (New) The epitaxial growth method as claimed in claim 19, wherein the substrate for growth is an InP substrate.

24. (New) A substrate for epitaxial growth used for an epitaxial growth method in which a compound semiconductor layer comprising 3 or 4 elements is formed on the substrate for growth by metal organic chemical vapor deposition, wherein an angle of gradient is 0.00° to 0.03° or 0.04° to 0.10° with respect to (100) direction in an entire effective area of the substrate.

25. (New) The substrate for epitaxial growth as claimed in claim 24, wherein the substrate is a semiconductor crystal substrate having dislocation density of $5000cm^{-2}$ or less.

26. (New) The substrate for epitaxial growth as claimed in claim 24, wherein the substrate is an InP substrate.

27. (New) The substrate for epitaxial growth as claimed in claim 25, wherein the substrate is an InP substrate.